HFZT

2SA1298

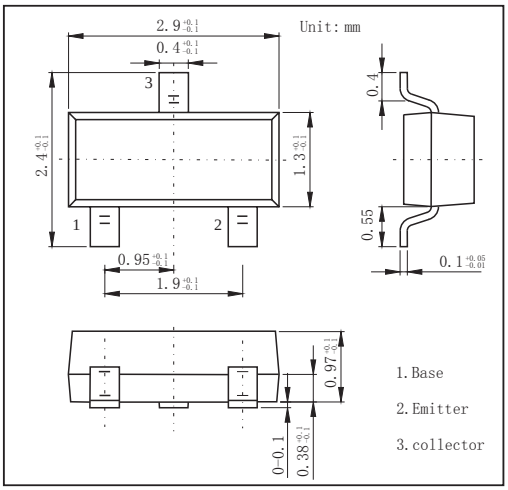
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Collector Current Capability IC=-0.8A
- Collector Emitter Voltage VCEO=-30V
- Low Frequency Power Amplifier Application
- Power Swithing Applications
- Complementary to 2SC3265
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

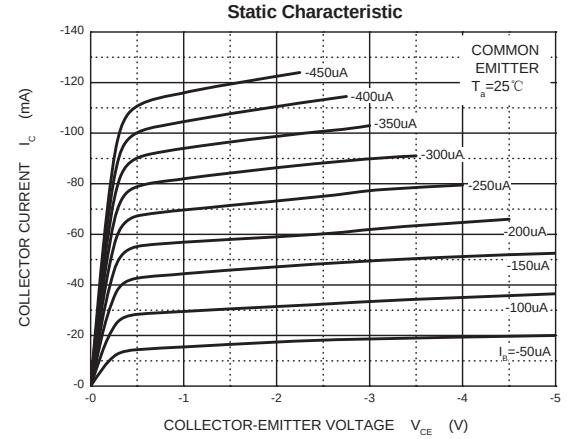
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-35	V
Collector - Emitter Voltage	V_{CEO}	-30	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-800	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

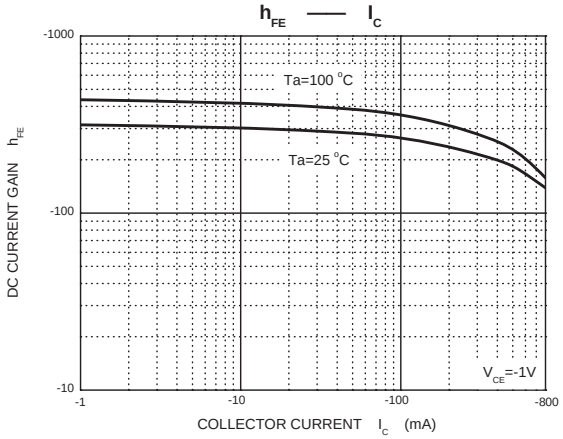
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -1mA， I_E=0	-35			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA， I_B=0	-30			
Emitter - base breakdown voltage	V_{EBO}	I_E= -1mA， I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -30 V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-20mA			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500 mA, I_B=-20mA			-1.2	
Base - emitter voltage	V_{BE}	V_{CE}=-1V,I_C= -10 mA			-0.8	
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -100mA	100		320	
	$h_{FE(2)}$	V_{CE}=- 1V, I_C= -800mA	40			
Collector output capacitance	C_{ob}	V_{CB}= -6V, I_E= 0,f=1MHz		13		pF
Transition frequency	f_T	V_{CE}= -5V, I_C= -10mA		120		MHz

RATINGS AND CHARACTERISTIC CURVES

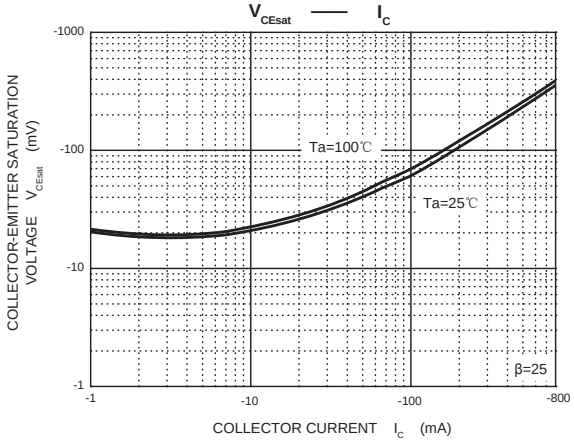
Static Characteristic



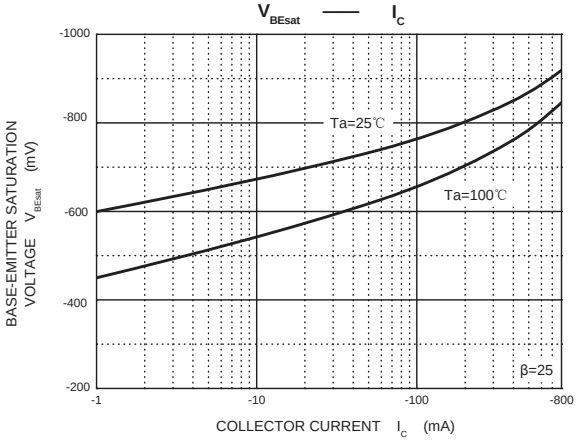
h_{FE} —— I_C



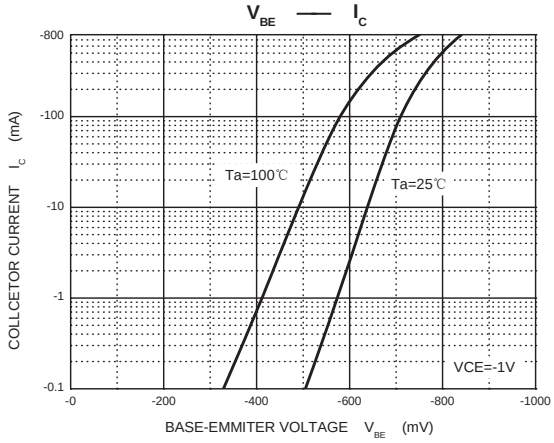
V_{CEsat} —— I_C



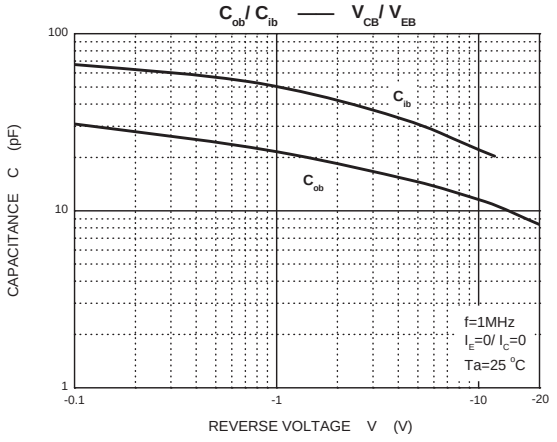
V_{BEsat} —— I_C



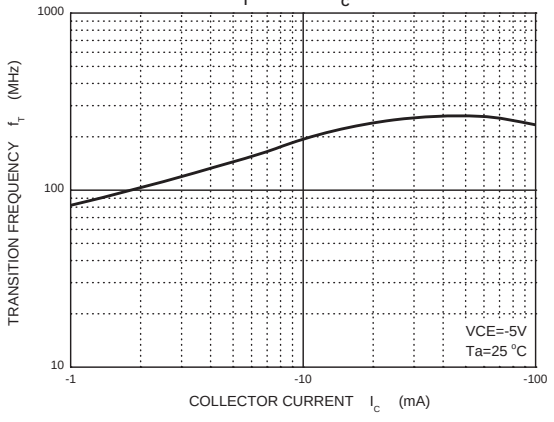
V_{BE} —— I_C



C_{ob} / C_{ib} —— V_{CB} / V_{EB}



f_T —— I_C



P_C —— T_a